

Title (en)

AN ECPR MASTER ELECTRODE AND A METHOD FOR PROVIDING SUCH ECPR MASTER ELECTRODE

Title (de)

ECPR-MASTERELEKTRODE UND VERFAHREN ZUR BEREITSTELLUNG SOLCH EINER MASTERELEKTRODE

Title (fr)

ÉLECTRODE-MAÎTRE DE TYPE ECPR (RÉPLICATION ÉLECTROCHIMIQUE DES MOTIFS) ET PROCÉDÉ POUR OBTENIR UNE TELLE ÉLECTRODE-MAÎTRE DE TYPE ECPR

Publication

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Application

EP 10795731 A 20101223

Priority

EP 2010070646 W 20101223

Abstract (en)

[origin: WO2012084047A1] An ECPR master electrode(10) and a method for providing such master electrode is provided. The master electrode comprises a carrier element (20) having an electrically conducting electrode surface(23) on a backside (21) and a topographical pattern (30) with an at least partly electrically insulating top (32) on a frontside (22) of said carrier element (20), said topographical pattern (30) is forming at least one electrochemical cell (34) in said carrier element, said electrochemical cell comprising a bottom (36) and at least one side wall (38), said bottom having an electrically conducting surface (40) being conductively connected to the electrically conducting electrode surface (23) on the back side (21) through the carrier element (20), wherein said at least one side wall (38) in said carrier element (20) is at least partly covered by an electrically insulating layer (42).

IPC 8 full level

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CPC (source: EP US)

H01L 21/2885 (2013.01 - EP US); **H05K 3/205** (2013.01 - EP)

Citation (search report)

See references of WO 2012084047A1

Citation (examination)

- KITAZOE M ET AL: "A layer-by-layer Cat-CVD of conformal and stoichiometric silicon nitride with in-situ H² post-treatment", THIN SOLID FILMS, ELSEVIER, AMSTERDAM, NL, vol. 501, no. 1-2, 20 April 2006 (2006-04-20), pages 160 - 163, XP025006303, ISSN: 0040-6090, [retrieved on 20060420], DOI: 10.1016/J.TSF.2005.07.176
- WANG QI ET AL: "Conformal thin-film silicon nitride deposited by hot-wire chemical vapor deposition", APPLIED PHYSICS LETTERS, A I P PUBLISHING LLC, US, vol. 84, no. 3, 19 January 2004 (2004-01-19), pages 338 - 340, XP012061850, ISSN: 0003-6951, DOI: 10.1063/1.1640803

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